VITELIC

V53C664
64K x 16 BIT FAST PAGE MODE BYTE WRITE CMOS DYNAMIC RAM

PRELIMINARY

V53C664	80/80L	10/10L
Max. $\overline{RAS}$ Access Time, (t_{RAC})	80 ns	100 ns
Max. Column Address Access Time, (t_{CAA})	45 ns	55 ns
Min. Fast Page Mode Cycle Time, (t_{PC})	55 ns	65 ns
Min. Read/Write Cycle Time, (t_{RC})	135 ns	170 ns

LOW POWER V53C664L	80L	10L
Max. CMOS Standby Current, (I_{DD6})	200µA	200 µA

Features

- 64K by 16-bit organization
- $\overline{RAS}$ Access time: 80, 100 ns
- Low power dissipation
  - V53C664K10
    - — Operating Current – 90 mA max.
    - — TTL Standby Current – 2 mA max.
- Low CMOS Standby Current
  - V53C664 – 1.0 mA max.
  - V53C664L – 0.2 mA max.
- Low Battery Back-up Current
  - V53C664L – 300 µA max.
  - 200 µA with 64ms refresh interval available on request
- Fast Page, Byte-Write, Read-Modify-Write, $\overline{CAS}$ before $\overline{RAS}$ refresh, and $\overline{RAS}$-only refresh capability
- Refresh Interval
  - V53C664 – 256 cycles/4ms
  - V53C664L – 256 cycles/32ms
- Available in 40 Pin Plastic SOJ package

Description

The V53C664 is a new generation, 65,536 word x 16 bit CMOS dynamic RAM fabricated with Vitelic's VICMOS III technology. The 16-bit wide organization makes the V53C664 ideal for high bandwidth applications such as imaging and graphics. In addition, the version with very low standby current, V53C664L, is extremely suitable for portable applications such as laptop and notebook personal computers.

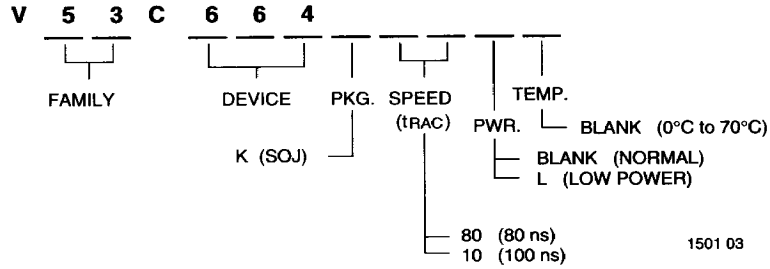
The V53C664 supports Fast Page Mode operation for high data bandwidth. Fast Page Mode allows 256 random accesses within a single row with access cycle times as short as 55 ns per 16-bit word. The addition of Byte Write control, of upper and lower byte, makes the V53C664 ideal for use in 16-, 32-bit wide data bus systems.

Mulitplexed address inputs and common input/output permit the V53C664 to be packaged in a standard 40 pin plastic SOJ to provide high system bit densities.

Device Usage Chart

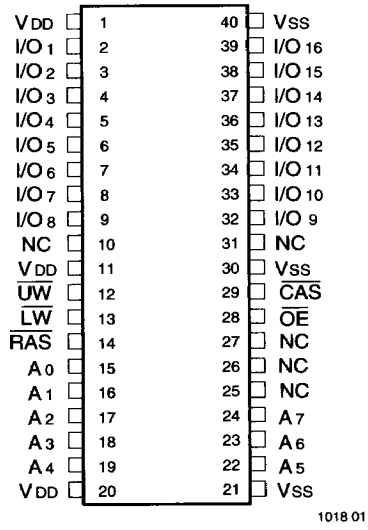
Operating Temperature Range	Package Outline	Access Time (ns)		Power		Temperature Mark
	K	80	100	Low	Std.	
0°C to 70°C	•	•	•	•	•	Blank

V53C664 Rev. 02 September 1991



Description	Pkg.	Pin Count
Plastic SOJ	K	40
Plastic ZIP	Z	40

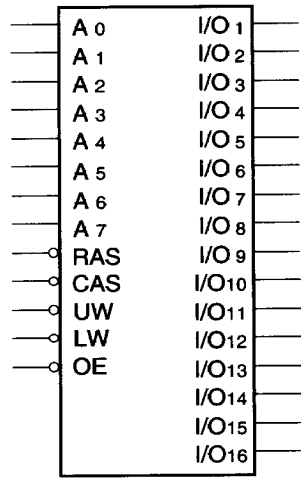
40-Pin Plastic SOJ
PIN CONFIGURATION
Top View



Pin Names

Symbol	Name
A0 – A7	Address Inputs
$\overline{RAS}$	Row Address Strobe
$\overline{CAS}$	Column Address Strobe
$\overline{UW}$	Read/Upper Byte Write Input
$\overline{LW}$	Read/Lower Byte Write Input
$\overline{OE}$	Output Enable
I/O1 – I/O16	Data Input/Output
V_{DD}	Power (+ 5V)
V_{SS}	Ground
NC	No Connection

Logic Symbol



Absolute Maximum Ratings*

Ambient Temperature
Under Bias .....–10°C to +80°C
Storage Temperature (plastic) ....–55°C to +125°C
Voltage Relative to V_{SS} .....–1.0 to +7.0 V
Data Out Current .....50 mA
Power Dissipation .....1.0 W

*Note: Operation above Absolute Maximum Ratings can adversely affect device reliability.

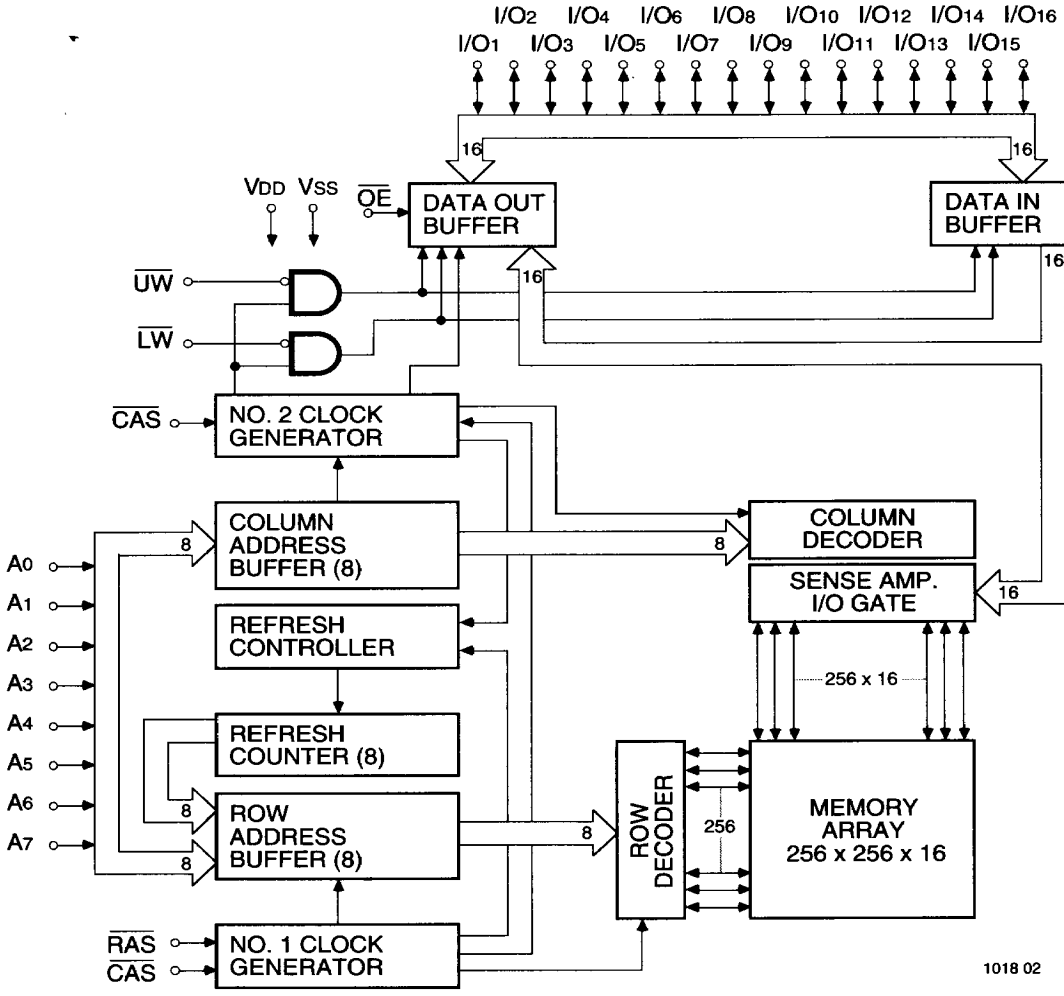
Capacitance*

V_{DD} = 5V ± 10%, V_{SS} = 0V

Symbol	Parameter	Min.	Max.	Unit
C_{IN1}	Input Capacitance (A0 – A7)	3	4	pF
C_{IN2}	Input Capacitance ($\overline{RAS}$, $\overline{CAS}$, $\overline{UW}$, $\overline{LW}$, $\overline{OE}$)	4	5	pF
C_{OUT}	Output Capacitance (I/O1 – I/O16)	5	7	pF

*NOTE: Capacitance is sampled and not 100% tested

Block Diagram



DC and Operating Characteristics

T_A = 0°C to 70°C, V_{DD} = 5 V ±10%, V_{SS} = 0 V, unless otherwise specified.

Symbol	Parameter	Access Time	V53C664			V53C664L			Unit	Test Conditions	Notes
			Min.	Typ.	Max.	Min.	Typ.	Max.			
I_{LI}	Input Leakage Current (any input pin)		−10		10	−10		10	µA	$V_{SS} \le V_{IN} \le V_{DD}$	
I_{LO}	Output Leakage Current (for High-Z State)		−10		10	−10		10	µA	$V_{SS} \le D_{OUT} \le V_{DD}$ $\overline{RAS}$,$\overline{CAS}$ at V_{IH}	
I_{DD1}	V_{DD} Supply Current, Operating	80			115			115	mA	$t_{RC} = t_{RC}$ (min.)	1,2
		100			90			90			
I_{DD2}	V_{DD} Supply Current, TTL Standby				2.0			2.0	mA	$\overline{RAS}$,$\overline{CAS}$ at V_{IH} other inputs ≥ V_{SS}	
I_{DD3}	V_{DD} Supply Current, $\overline{RAS}$-Only Refresh	80			115			115	mA	$t_{RC} = t_{RC}$ (min.)	2
		100			90			90			
I_{DD4}	V_{DD} Supply Current, Fast Page Mode Operation	80			100			100	mA	Minimum Cycle	1,2
		100			90			90			
I_{DD5}	V_{DD} Supply Current, Standby, Output Enabled				5.0			5.0	mA	$\overline{RAS}$=V_{IH},$\overline{CAS}$=V_{IL} other inputs ≥ V_{SS}	1
I_{DD6}	V_{DD} Supply Current, CMOS Standby				1.0			0.2	mA	$\overline{RAS} \ge V_{DD}$−0.2 V, $\overline{CAS} \ge V_{DD}$ − 0.2V, other inputs ≥ V_{SS}	
I_{DD7}*	Battery Backup Data Retention Current (only "L" Version)				N.A.			0.3*	mA	$\overline{CAS}$-Before-$\overline{RAS}$ Refresh cycles t_{RC} = 125 µs CMOS clock levels	18
V_{IL}	Input Low Voltage		−1		0.8	−1		0.8	V		3
V_{IH}	Input High Voltage		2.4		V_{DD} +1	2.4		V_{DD} +1	V		3
V_{OL}	Output Low Voltage				0.4			0.4	V	I_{OL} = -2.5 mA	

*I_{DD7} = 0.2 mA max. with t_{RC} = 250µs (64ms refresh interval) available on request.

AC Characteristics

T_A = 0°C to 70°C, V_{DD} = 5V ± 10%, V_{SS} = 0V unless otherwise noted
AC Test conditions, input pulse levels 0 to 3 V

#	JEDEC Symbol	Symbol	Parameter	80 Min.	80 Max.	100 Min.	100 Max.	Unit	Notes
1	t_{RL1RH1}	t_{RAS}	$\overline{RAS}$ Pulse Width	80	75K	100	75K	ns	
2	t_{RL2RL2}	t_{RC}	Read or Write Cycle Time	135	—	170	—	ns	
3	t_{RH2RL2}	t_{RP}	$\overline{RAS}$ Precharge Time	45	—	60	—	ns	
4	t_{RL1CH1}	t_{CSH}	$\overline{CAS}$ Hold Time	80	—	100	—	ns	
5	t_{CL1CH1}	t_{CAS}	$\overline{CAS}$ Pulse Width	30	10K	35	10K	ns	
6	t_{RL1CL1}	t_{RCD}	$\overline{RAS}$ to $\overline{CAS}$ Delay	20	50	20	65	ns	4
7	t_{WH2CL2}	t_{RCS}	Read Command Setup Time	0	—	0	—	ns	
8	t_{AVRL2}	t_{ASR}	Row Address Setup Time	0	—	0	—	ns	
9	t_{RL1AX}	t_{RAH}	Row Address Hold Time	10	—	10	—	ns	
10	t_{AVCL2}	t_{ASC}	Column Address Setup Time	0	—	0	—	ns	
11	t_{CL1AX}	t_{CAH}	Column Address Hold Time	15	—	15	—	ns	
12	$t_{CL1RH1(R)}$	t_{RSHr}	$\overline{RAS}$ Hold Time (Read Cycle)	30	—	35	—	ns	
13	t_{CH2RL2}	t_{CRP}	$\overline{CAS}$ to $\overline{RAS}$ Precharge Time	5	—	5	—	ns	
14	t_{CH2WX}	t_{RCH}	Read Command Hold Time referenced to $\overline{CAS}$	0	—	0	—	ns	5
15	t_{RH2WX}	t_{RRH}	Read Command Hold Time referenced to $\overline{RAS}$	0	—	0	—	ns	5
16	$t_{OEL1RH2}$	t_{ROH}	$\overline{RAS}$ Hold Time referenced to $\overline{OE}$	10	—	10	—	ns	
17	t_{GL1QV}	t_{OAC}	Access Time from $\overline{OE}$	—	25	—	30	ns	
18	t_{CL1QV}	t_{CAC}	Access Time from $\overline{CAS}$	—	30	—	35	ns	6, 7
19	t_{RL1QV}	t_{RAC}	Access Time from $\overline{RAS}$	—	80	—	100	ns	6, 8, 9
20	t_{AVQV}	t_{CAA}	Access Time from Column Address	—	45	—	55	ns	6, 7, 10
21	t_{CL1QX}	t_{LZ}	$\overline{CAS}$ to Output in Low-Z	0	—	0	—	ns	16
22	t_{CH2QZ}	t_{HZ}	$\overline{OE}$ or $\overline{CAS}$ to High-Z Output	0	25	0	25	ns	16
23	t_{RL1AX}	t_{AR}	Column Address Hold Time referenced to $\overline{RAS}$	55	—	65	—	ns	
24	t_{RL1AV}	t_{RAD}	$\overline{RAS}$ to Column Address Delay Time	15	35	15	45	ns	11
25	$t_{CL1RH1(W)}$	t_{RSHw}	RAS or CAS Hold Time in Write Cycle	30	—	35	—	ns	
26	t_{WL1CH1}	t_{CWL}	Write Command to $\overline{CAS}$ Lead Time	20	—	20	—	ns	
27	t_{WL1CL2}	t_{WCS}	Write Command Set-Up Time	0	—	0	—	ns	12, 13
28	t_{CL1WH1}	t_{WCH}	Write Command Hold Time	15	—	15	—	ns	
29	t_{WL1WH1}	t_{WP}	Write Pulse Width	15	—	15	—	ns	
30	t_{RL1WH1}	t_{WCR}	Write Command Hold Time from $\overline{RAS}$	55	—	65	—	ns	
31	t_{WL1RH1}	t_{RWL}	Write Command to RAS Lead Time	20	—	20	—	ns	

AC Characteristics (continued)

#	JEDEC Symbol	Symbol	Parameter	80 Min.	80 Max.	100 Min.	100 Max.	Unit	Notes
32	t_{DVWL2}	t_{DS}	Data-In Set-Up Time	0	—	0	—	ns	14
33	t_{WL1DX}	t_{DH}	Data-In Hold Time	15	—	15	—	ns	14
34	t_{WL1GL2}	t_{WOH}	$\overline{OE}$ Hold Time	10		10		ns	14
35	t_{GH2DX}	t_{OED}	$\overline{OE}$ to Data Delay Time	10	—	20	—	ns	
36	t_{RL2RL2} (RMW)	t_{RWC}	Read-Modify-Write Cycle Time	175	—	220	—	ns	
37	t_{RL2RH1} (RMW)	t_{RRW}	Read-Modify-Write Cycle $\overline{RAS}$ Pulse Width	120	—	150	—	ns	
38	t_{CL1WL2}	t_{CWD}	$\overline{CAS}$ to $\overline{WE}$ Delay	50	—	65	—	ns	12
39	t_{RL1WL2}	t_{RWD}	$\overline{RAS}$ to $\overline{WE}$ Delay Time in Read-Modify-Write Cycle	100	—	130	—	ns	12
40	t_{CL1CH1}	t_{CRW}	$\overline{CAS}$ Pulse Width (RMW)	80	—	95	—	ns	
41	t_{AVWL2}	t_{AWD}	Column Address to $\overline{WE}$ Delay	65	—	85	—	ns	12
42	t_{CL2CL2}	t_{PC}	Fast Page Mode Read or Write Cycle Time	55	—	65	—	ns	
43	t_{CH2CL2}	t_{CP}	$\overline{CAS}$ Precharge Time	10	—	10	—	ns	
44	t_{AVRH1}	t_{CAR}	Column Address to $\overline{RAS}$ Setup Time	45	—	55	—	ns	
45	t_{CH2QV}	t_{CAP}	Access Time from Column Precharge	—	50	—	60	ns	7
46	t_{RL1DX}	t_{DHR}	Data Hold Time referenced to $\overline{RAS}$	55	—	65	—	ns	
47	t_{CL1RL2}	t_{CSR}	$\overline{CAS}$ Setup Time ($\overline{CAS}$ before $\overline{RAS}$ Refresh)	5	—	5	—	ns	
48	t_{RH2CL2}	t_{RPC}	$\overline{RAS}$ to $\overline{CAS}$ Precharge Time	0	—	0	—	ns	
49	t_{RL1CH1}	t_{CHR}	$\overline{CAS}$ Hold Time ($\overline{CAS}$ before $\overline{RAS}$ Refresh)	10	—	10	—	ns	
50	t_{CL2CL2} (RMW)	t_{PCM}	Fast Page Mode Read-Modify-Write Cycle Time	100	—	120	—	ns	
51	t_{WH2CL2}	t_{MCS}	Byte-Masked Write Setup Time	0		0		ns	
52	t_{RH2WL2}	t_{MRH}	Byte-Masked Write Hold Time Referenced to $\overline{RAS}$	0		0		ns	
53	t_{CH2WL2}	t_{MCH}	Byte-Masked Write Hold Time Referenced to $\overline{RAS}$	0		0		ns	
		t_T	Transition Time (Rise and Fall)	3	50	3	50	ns	15
		t_{REF}	Refresh Interval (256 Cycles)	—	4	—	4	ms	17
		t_{REF}	Refresh Interval (256 Refresh Cycles, t_{RC} = 125 µs, V53C664L Only)	—	32	—	32	ms	17, 18

Notes:

1. I_{DD} is dependent on output loading when the device output is selected. Specified I_{DD} (max.) is measured with the output open.
2. I_{DD} is dependent upon the number of address transitions. Specified I_{DD} (max.) is measured with a maximum of two transitions per address cycle in First Page Mode.
3. Specified V_{IL} (min.) is steady state operation. During transitions, V_{IL} (min.) may undershoot to –1.0 V for periods not to exceed 20 ns. All AC parameters are measured with V_{IL} (min.) ≥ V_{SS} and V_{IH} (max.) ≤ V_{DD}.
4. t_{RCD} (max.) is specified for reference only. Operation within t_{RCD} (max.) and t_{RAD} (max.) limits ensure that t_{RAC} (max.) and t_{CAA} (max.) can be met. If t_{RCD} is greater than the specified t_{RCD} (max.), the access time is controlled by t_{CAA} and t_{CAC}.
5. Either t_{RRH} or t_{RCH} must be satisfied for a Read Cycle to occur.
6. Measured with a load equivalent to one TTL loads and 50 pF.
7. Access time is determined by the longer of t_{CAA}, t_{CAC}, or t_{CAP}.
8. Assumes that $t_{RAD} \leq t_{RAD}$ (max.). If t_{RAD} is greater than t_{RAD} (max.), t_{RAC} will increase by the amount that t_{RAD} exceeds t_{RAD} (max.).
9. Assumes that $t_{RCD} \leq t_{RCD}$ (max.). If t_{RCD} is greater than t_{RCD} (max.), t_{RAC} will increase by the amount that t_{RCD} exceeds t_{RCD} (max.).
10. Assumes that $t_{RAD} \geq t_{RAD}$ (max.).
11. Operation within the t_{RAD} (max.) limit ensures that t_{RAC} (max.) can be met. t_{RAD} (max.) is specified as a reference point only. If t_{RAD} is greater than the specified t_{RAD} (max.) limit, the access time is controlled by t_{CAA} and t_{CAC}.
12. t_{WCS}, t_{WHC}, t_{RWD}, t_{AWD} and t_{CWD} are not restrictive operating parameters.
13. t_{WCS} (min.) must be satisfied in an Early Write Cycle.
14. t_{DS} and t_{DH} are referenced to the later occurance of $\overline{CAS}$ or $\overline{WE}$.
15. t_T is measured between V_{IH} (min.) and V_{IL} (max.). AC measurements assume t_T = 5 ns.
16. Assumes a three-state test load (5pF and a 380 Ohm Thevenin equivalent).
17. An initial 200 µs pause and 8 $\overline{RAS}$-containing cycles are required when exiting an extended period of bias without clocks. An extended period of time without clocks is defined as one that exceeds the specified Refresh Interval.
18. This is battery backup data retention mode under $\overline{CAS}$-before-$\overline{RAS}$ refresh cycles.

    t_{RC} = 125 µs (125 µs x 256 = 32ms)

    $t_{RAS} = t_{RAS}$ (min) to 1µs

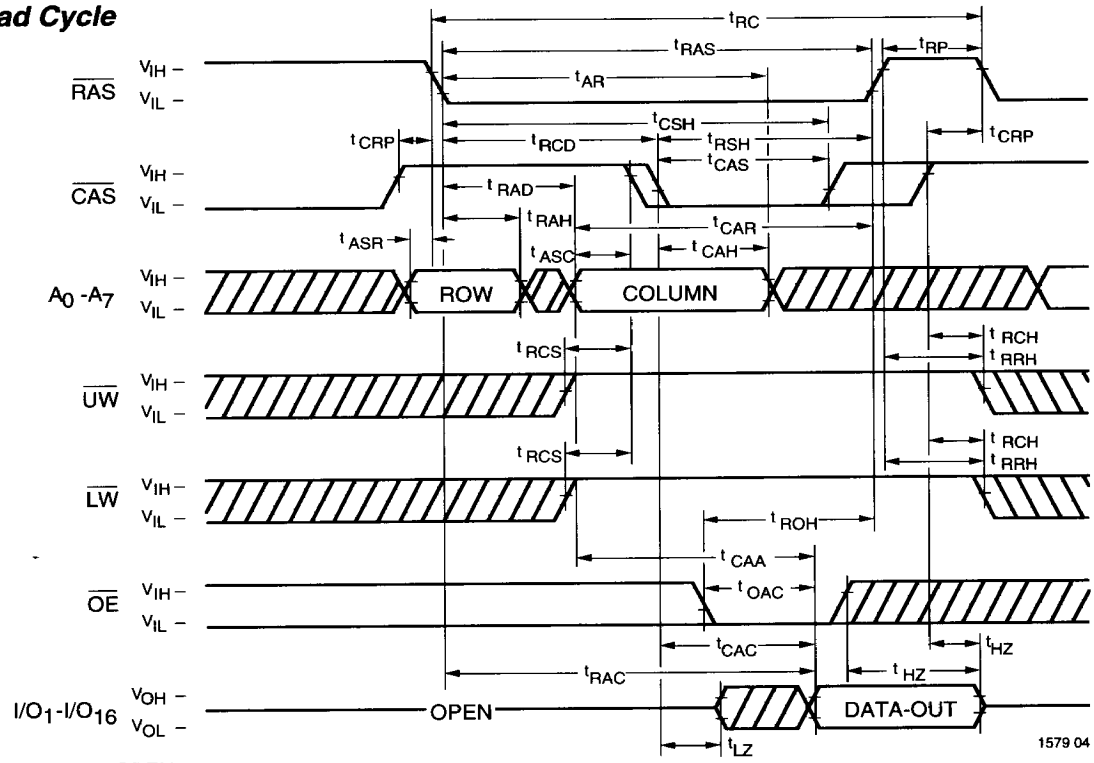
    Input voltages : $\overline{RAS}$ and $\overline{CAS}$ $V_{IH} > V_{DD} - 0.2$ V

    $V_{IL} < 0.2$ V

    $\overline{WE}$ and $\overline{OE}$ $V_{IN} > V_{DD} - 0.2$ V

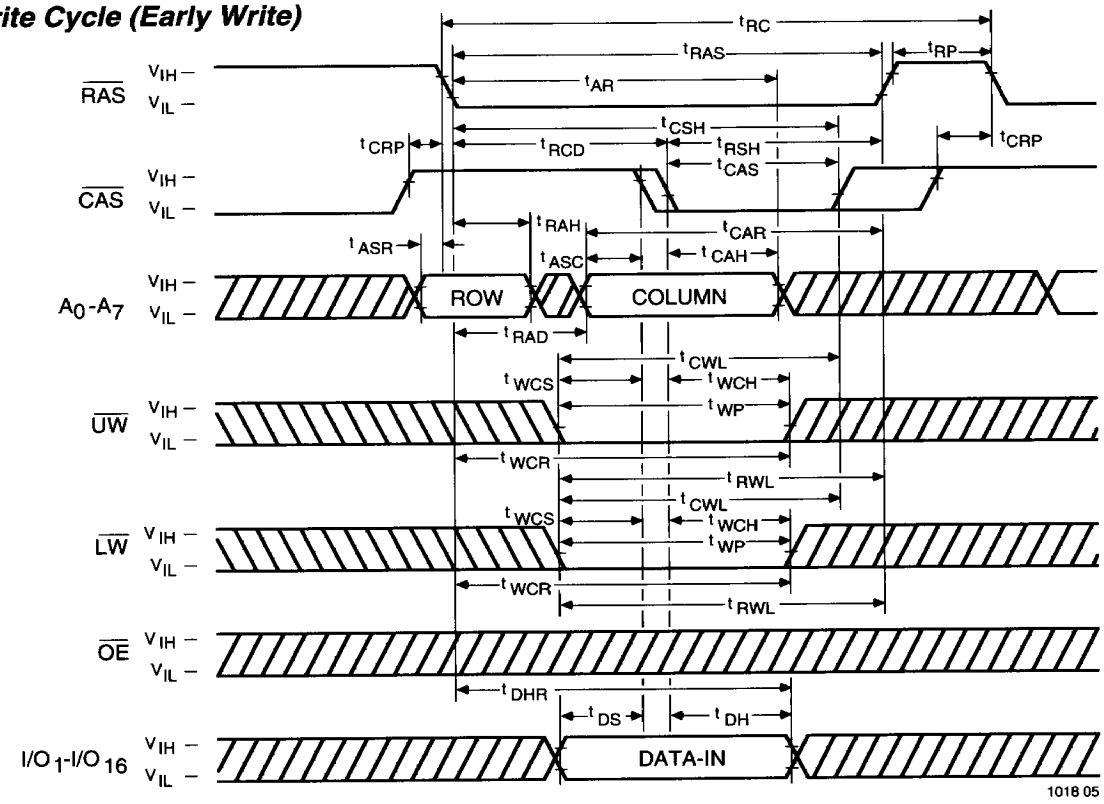
    All other inputs at stable V_{IH} or V_{IL}

Read Cycle



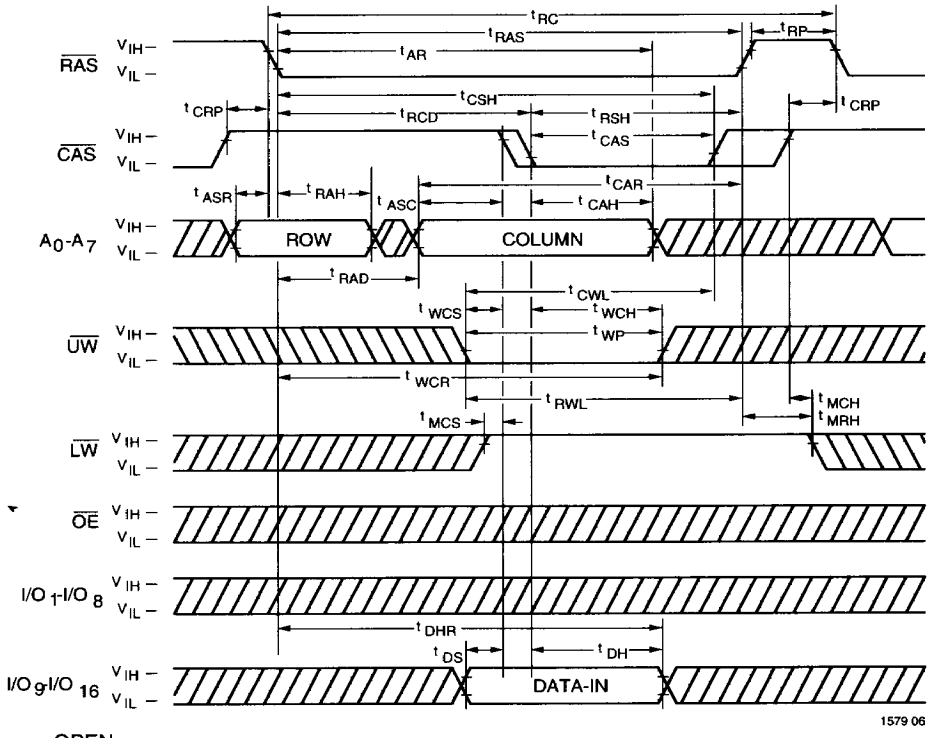
NOTE: D_{IN} = OPEN

Write Cycle (Early Write)



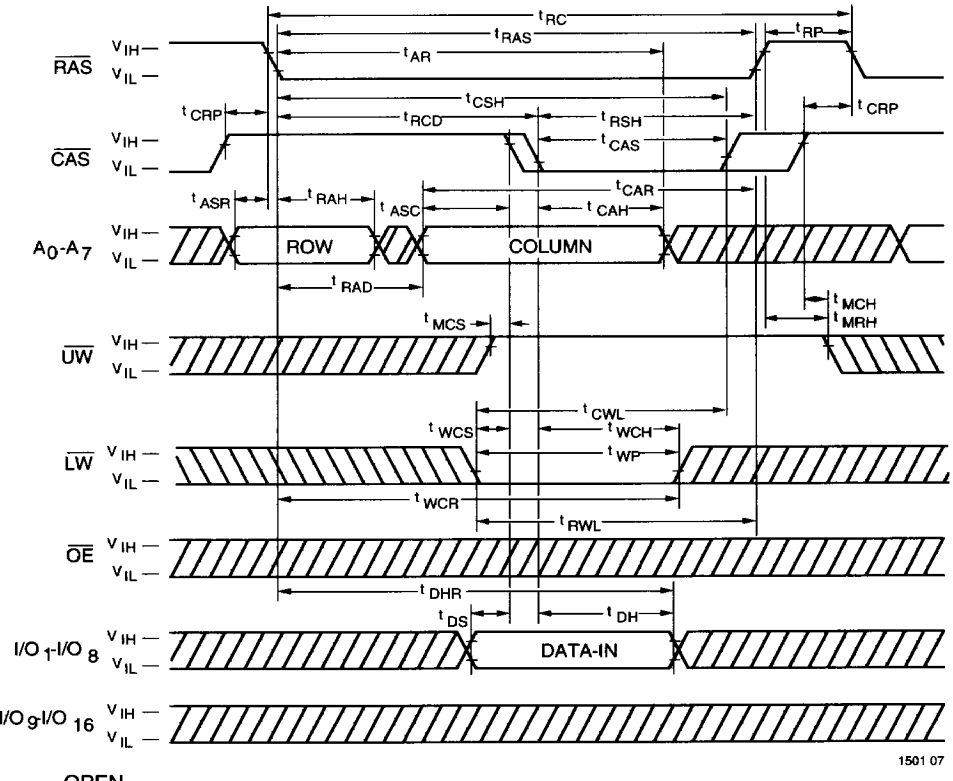
NOTE: D_{OUT} = OPEN

Upper Byte Write Cycle (Early Write)



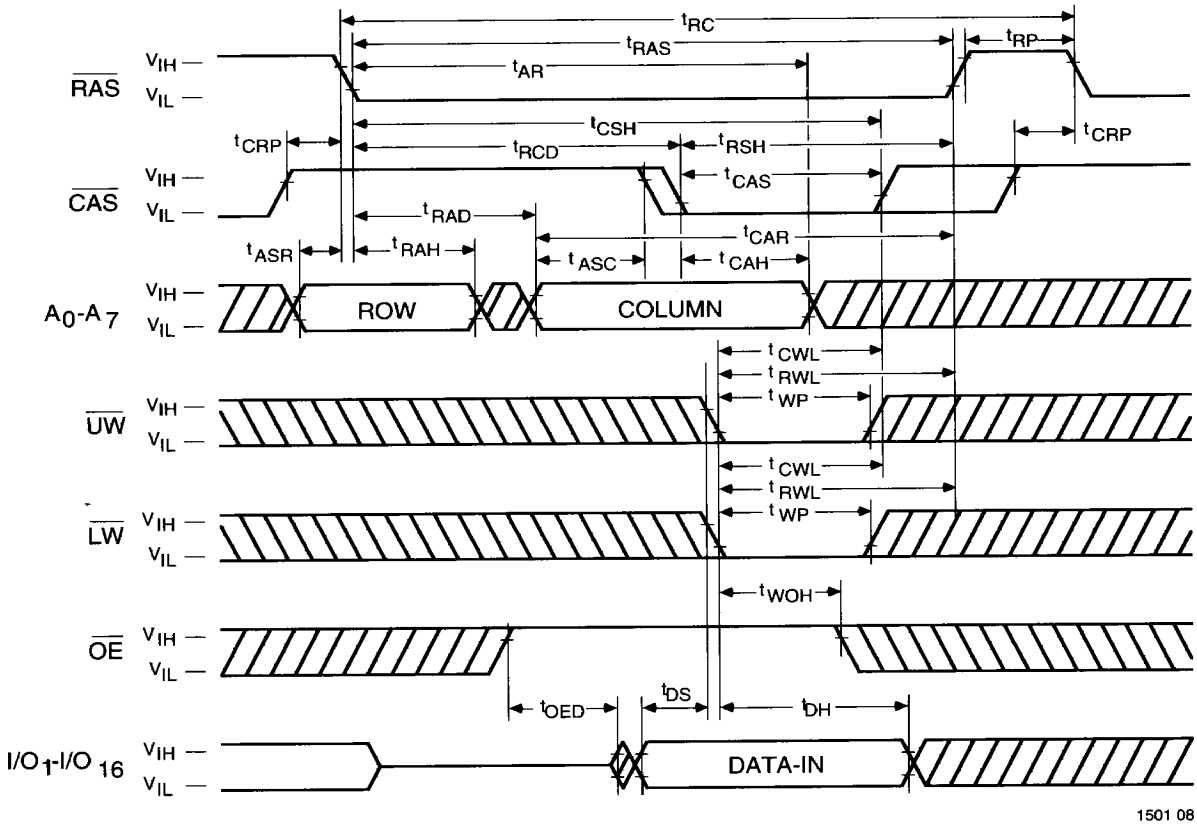
NOTE: D_{OUT} = OPEN

Lower Byte Write Cycle (Early Write)



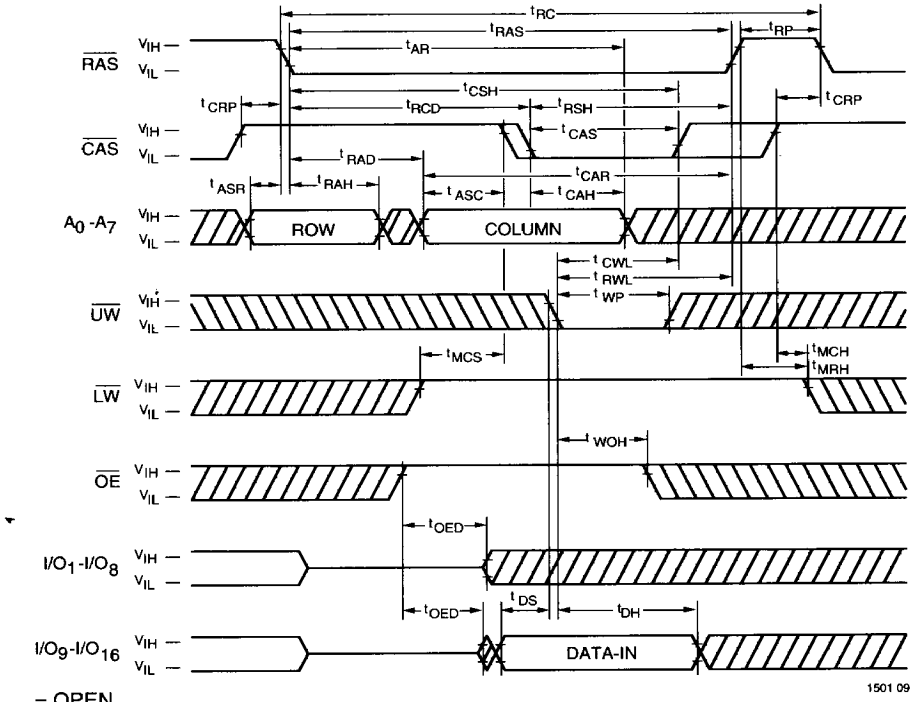
NOTE: D_{OUT} = OPEN

Write Cycle (OE-Controlled Write)



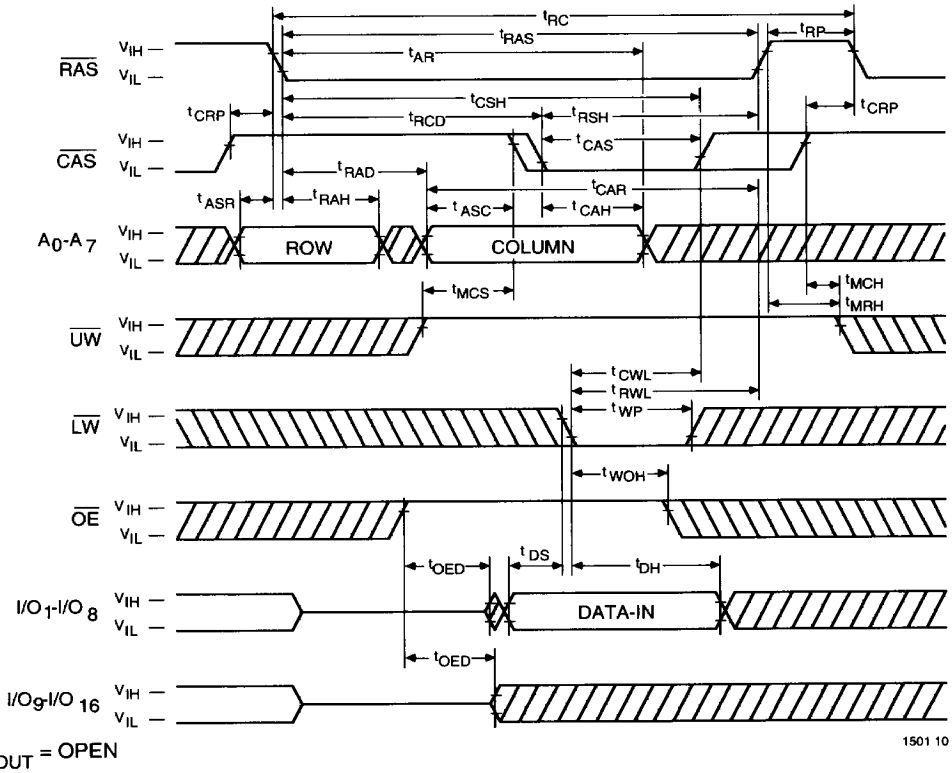
NOTE: D_{OUT} = OPEN

Upper Byte Write Cycle (OE-Controlled Write)



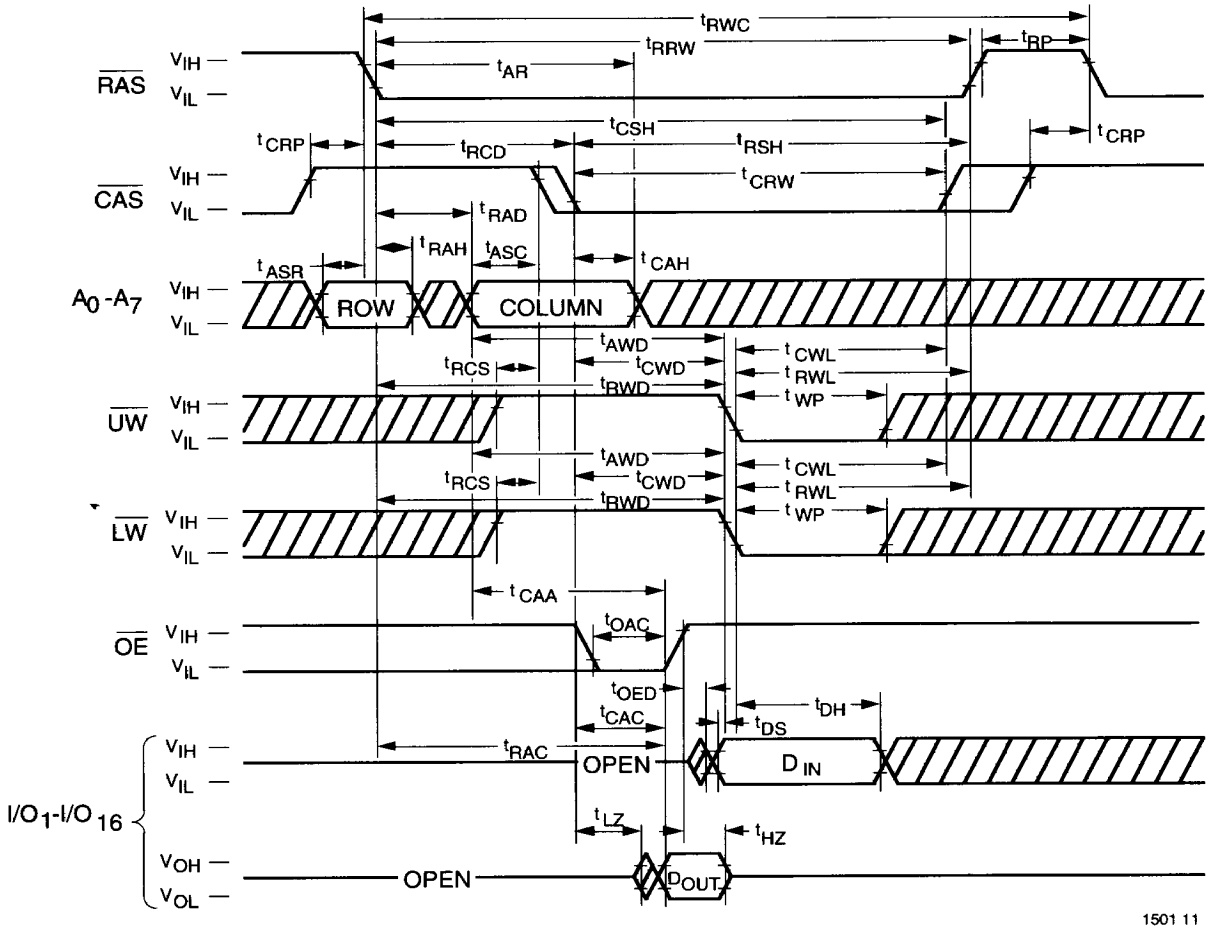
NOTE: D_{OUT} = OPEN

Lower Byte Write Cycle (OE-Controlled Write)

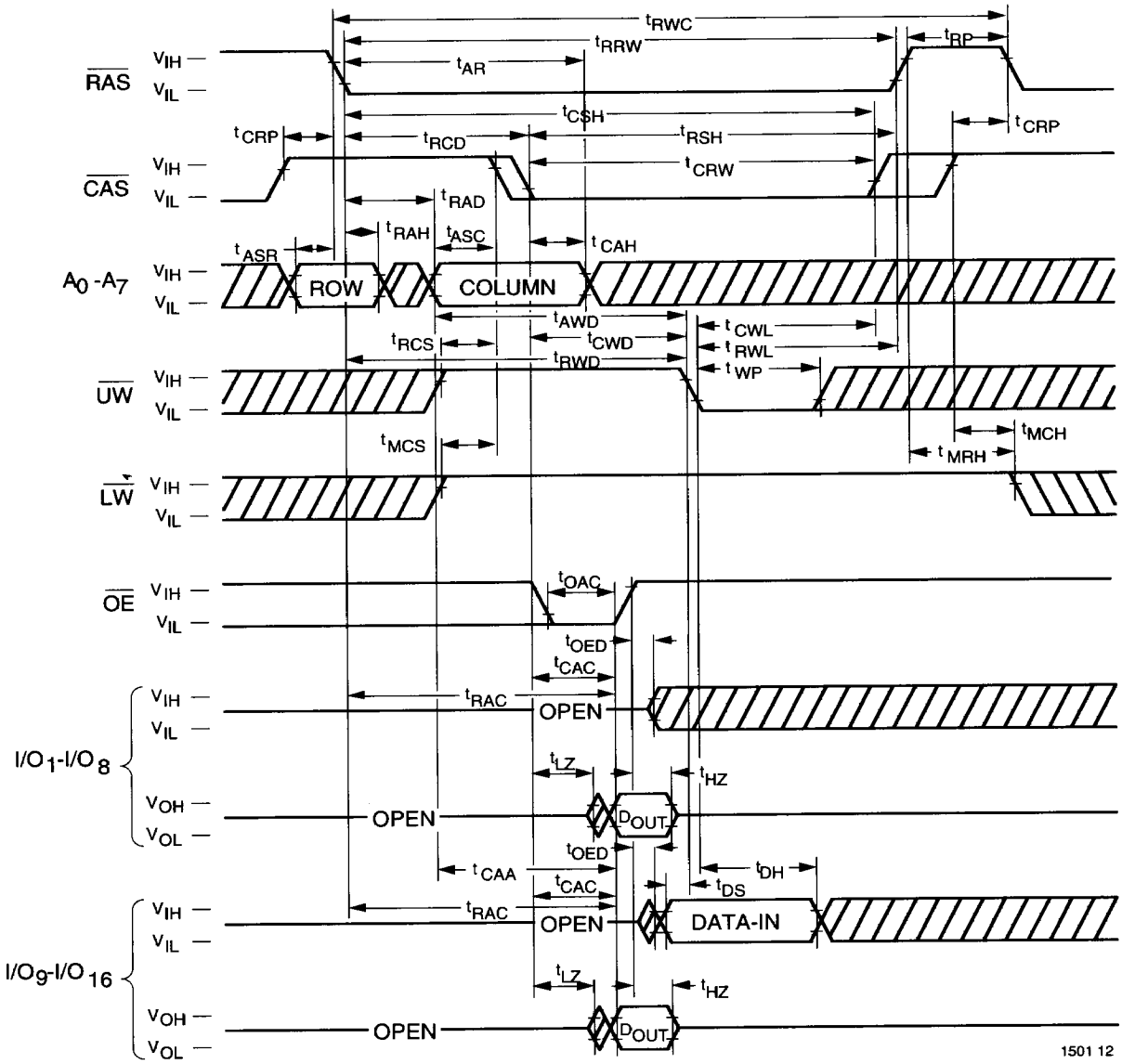


NOTE: D_{OUT} = OPEN

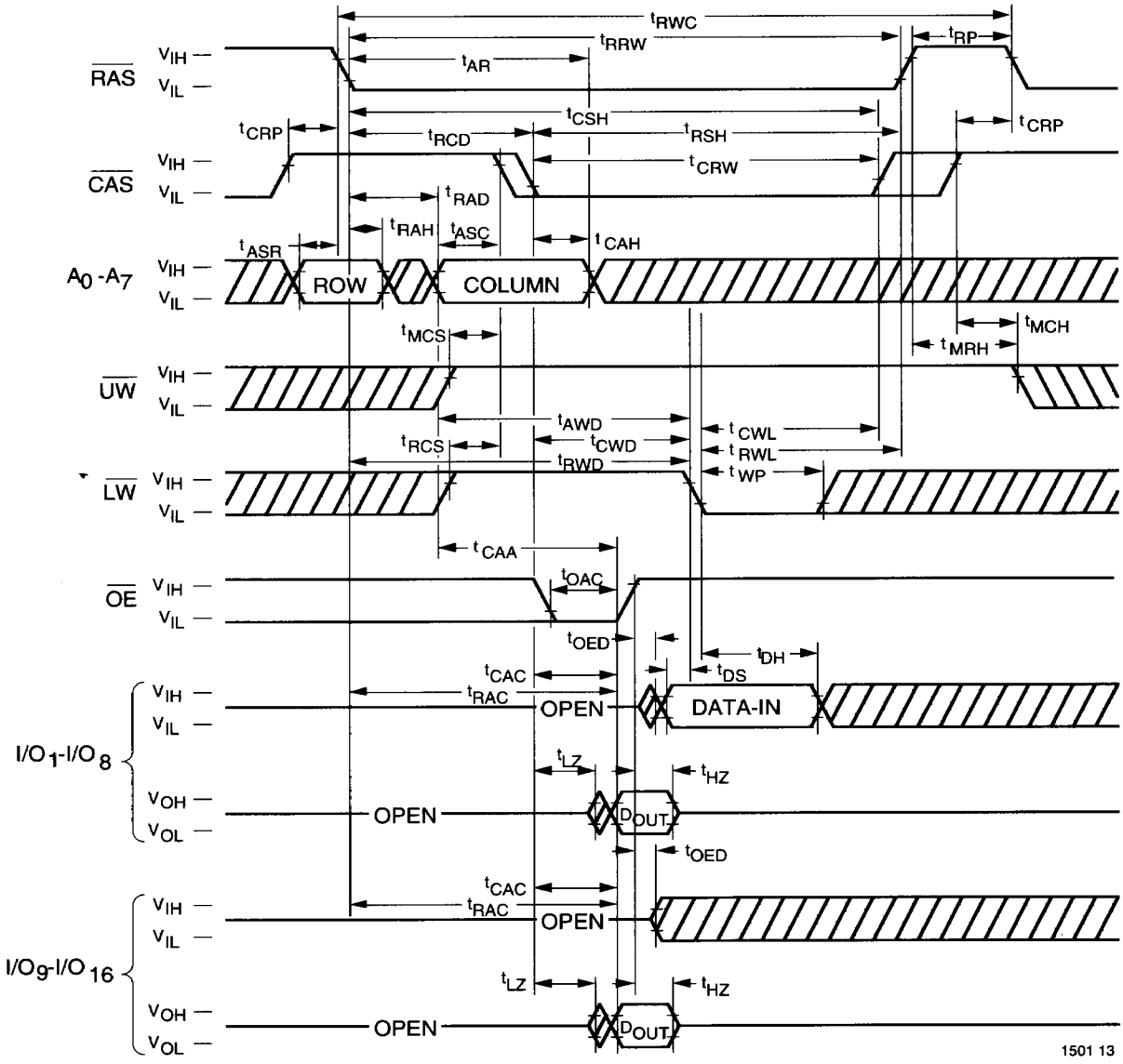
Read-Modify-Write Cycle



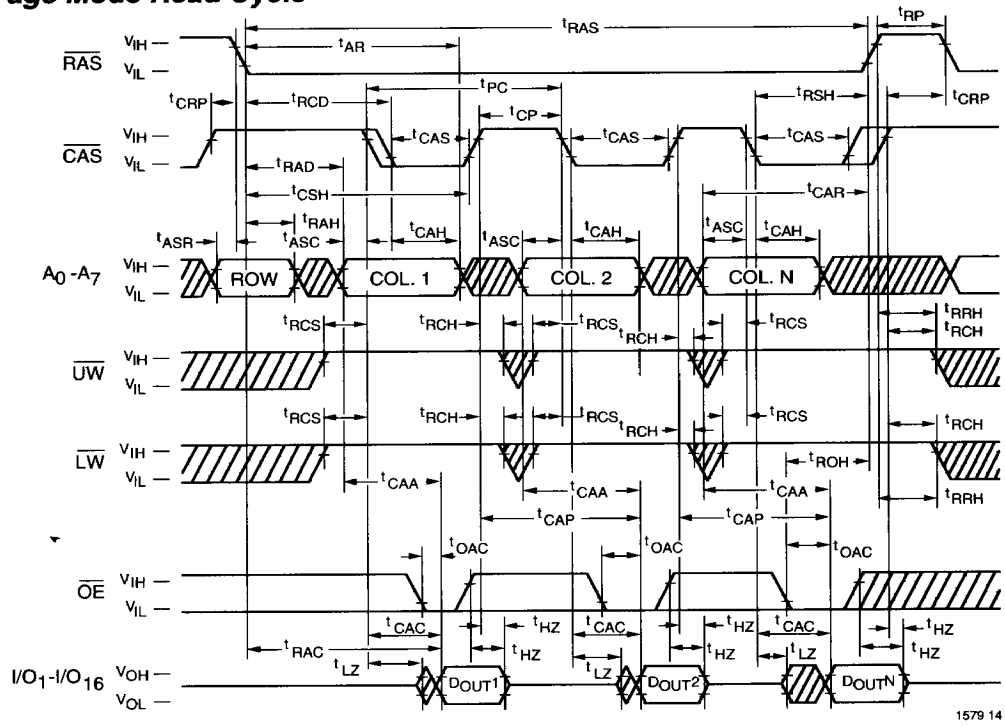
Read-Modify-Upper-Byte-Write Cycle



Read-Modify-Lower-Byte-Write Cycle

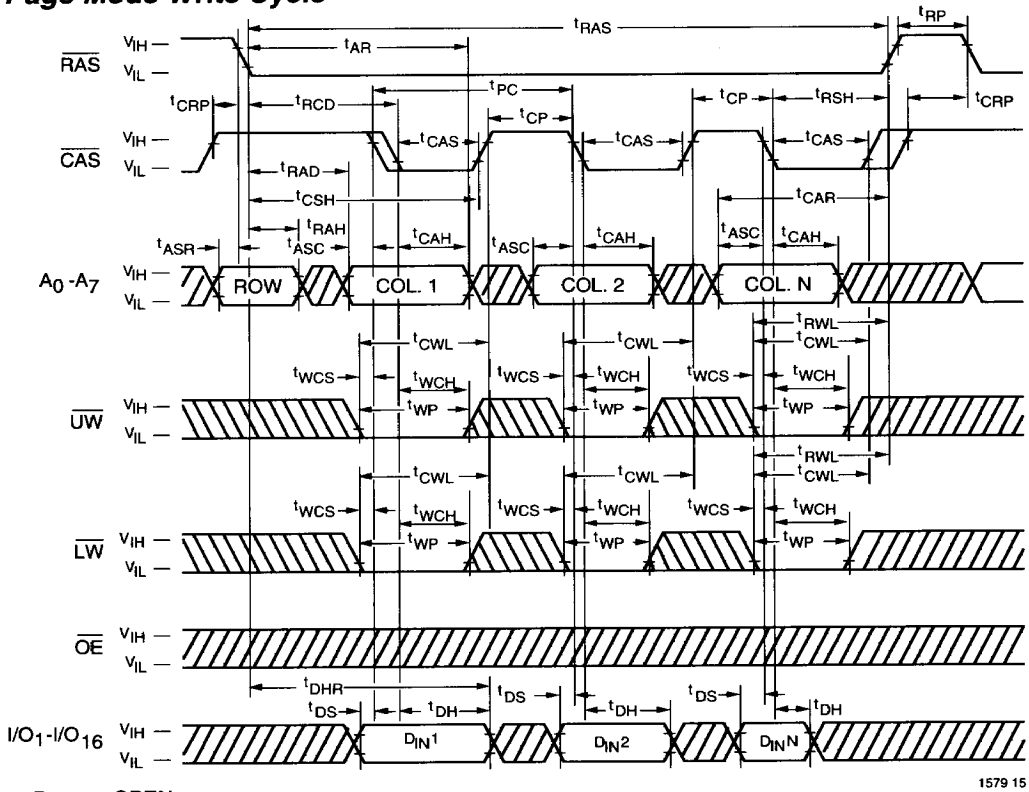


Fast Page Mode Read Cycle



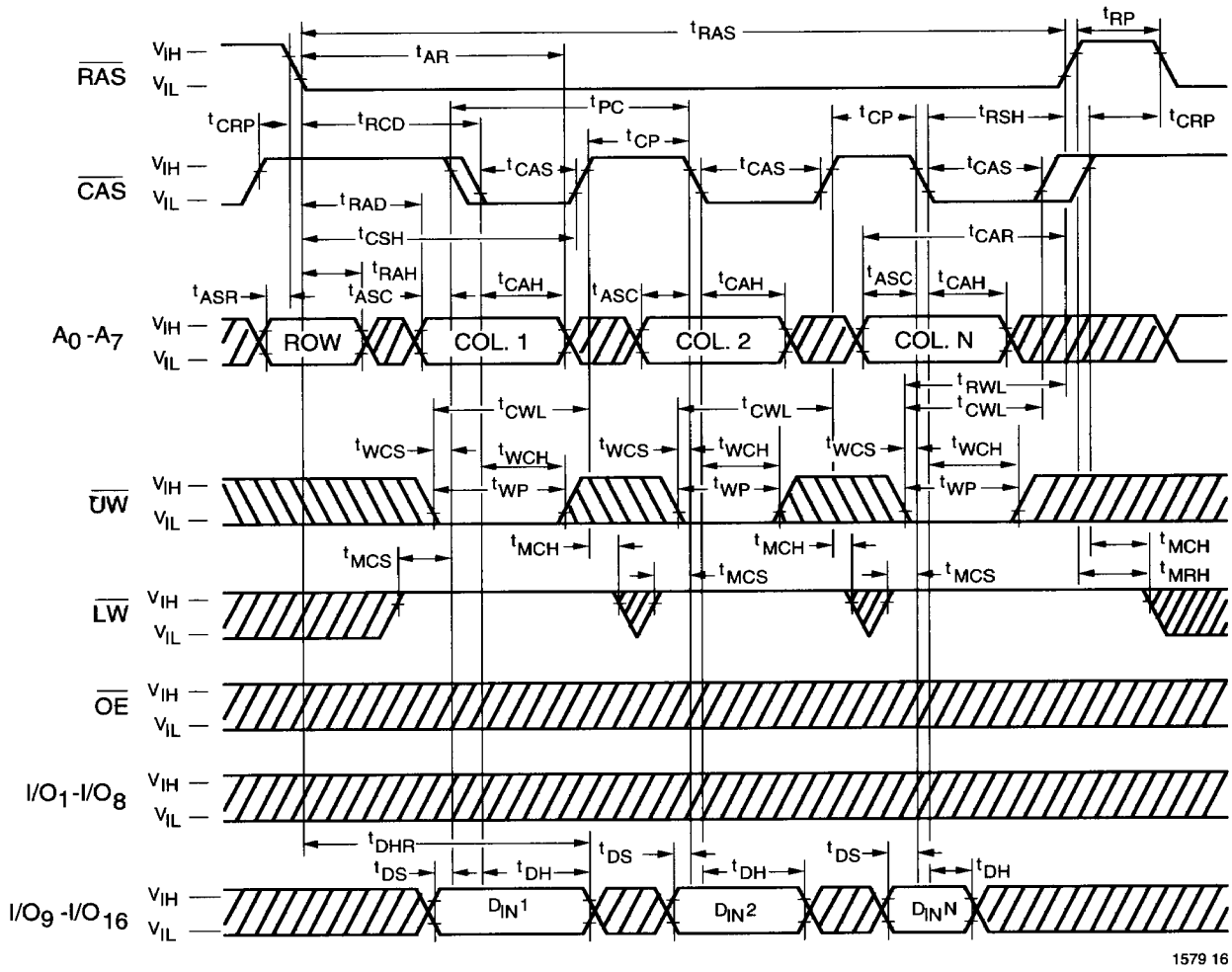
NOTE: D_{IN} = OPEN

Fast Page Mode Write Cycle



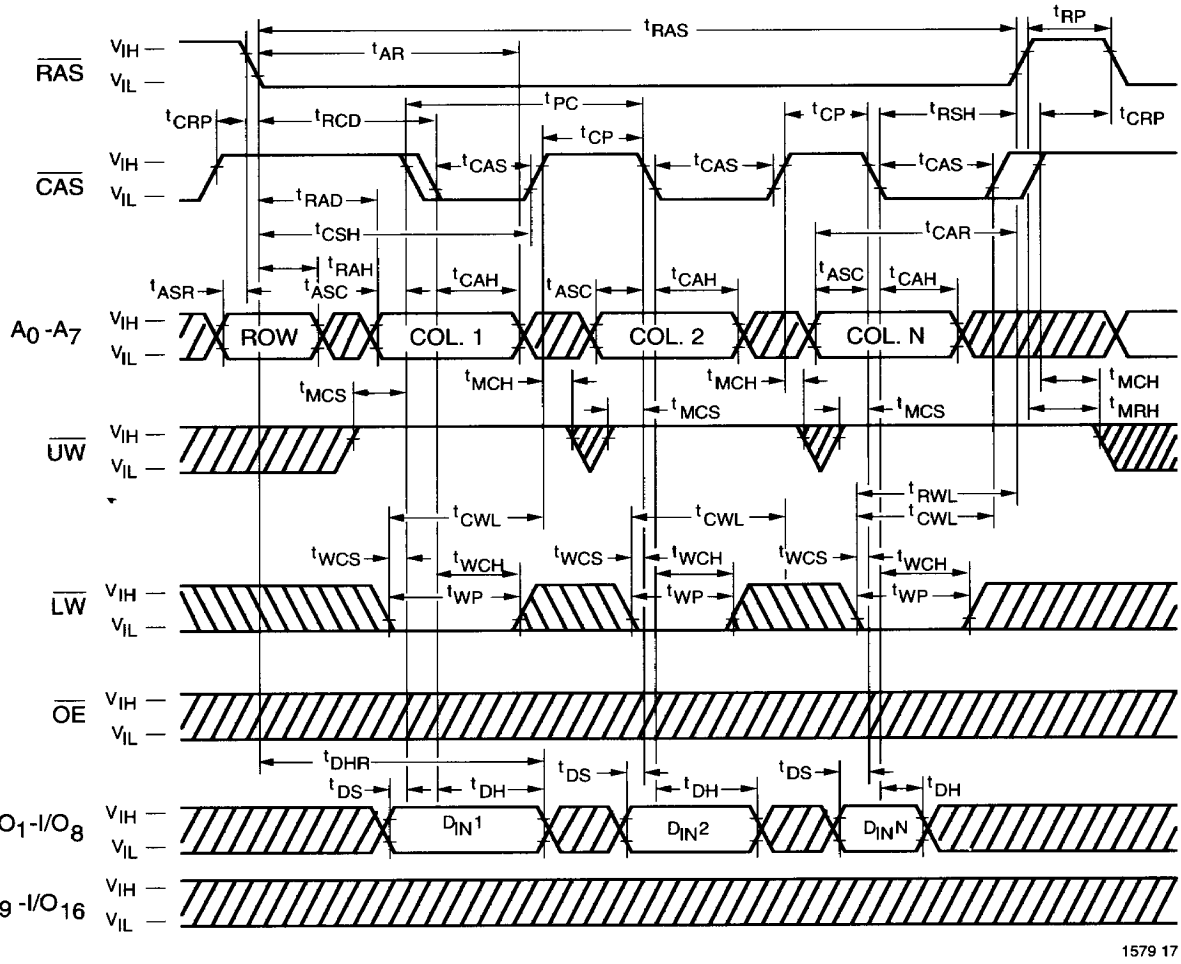
NOTE: D_{OUT} = OPEN

Fast Page Mode Upper Byte Write Cycle



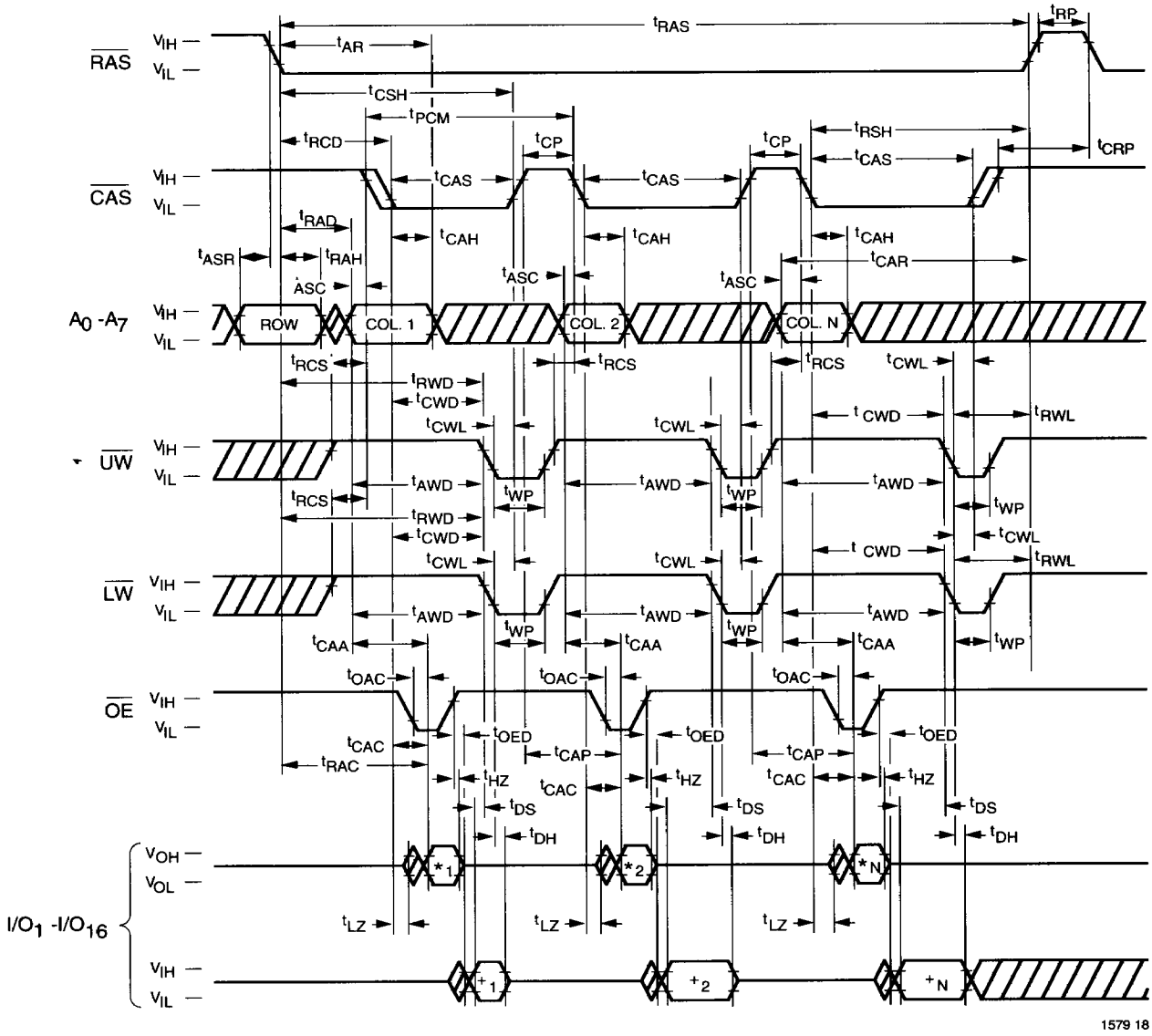
NOTE: D_{OUT} = OPEN

Fast Page Mode Lower Byte Write Cycle



NOTE: D_{OUT} = OPEN

Fast Page Read-Modify-Write Cycle



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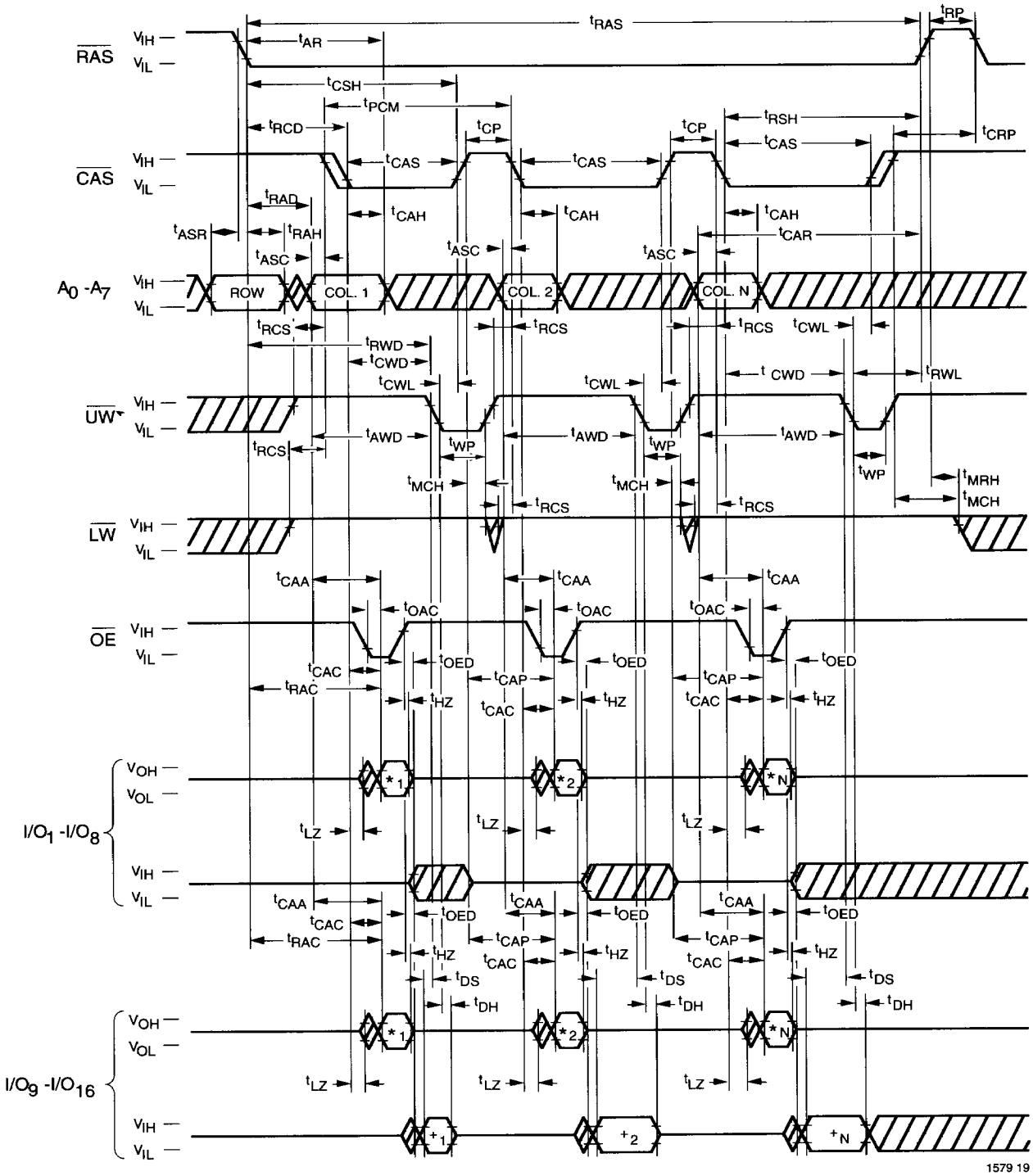
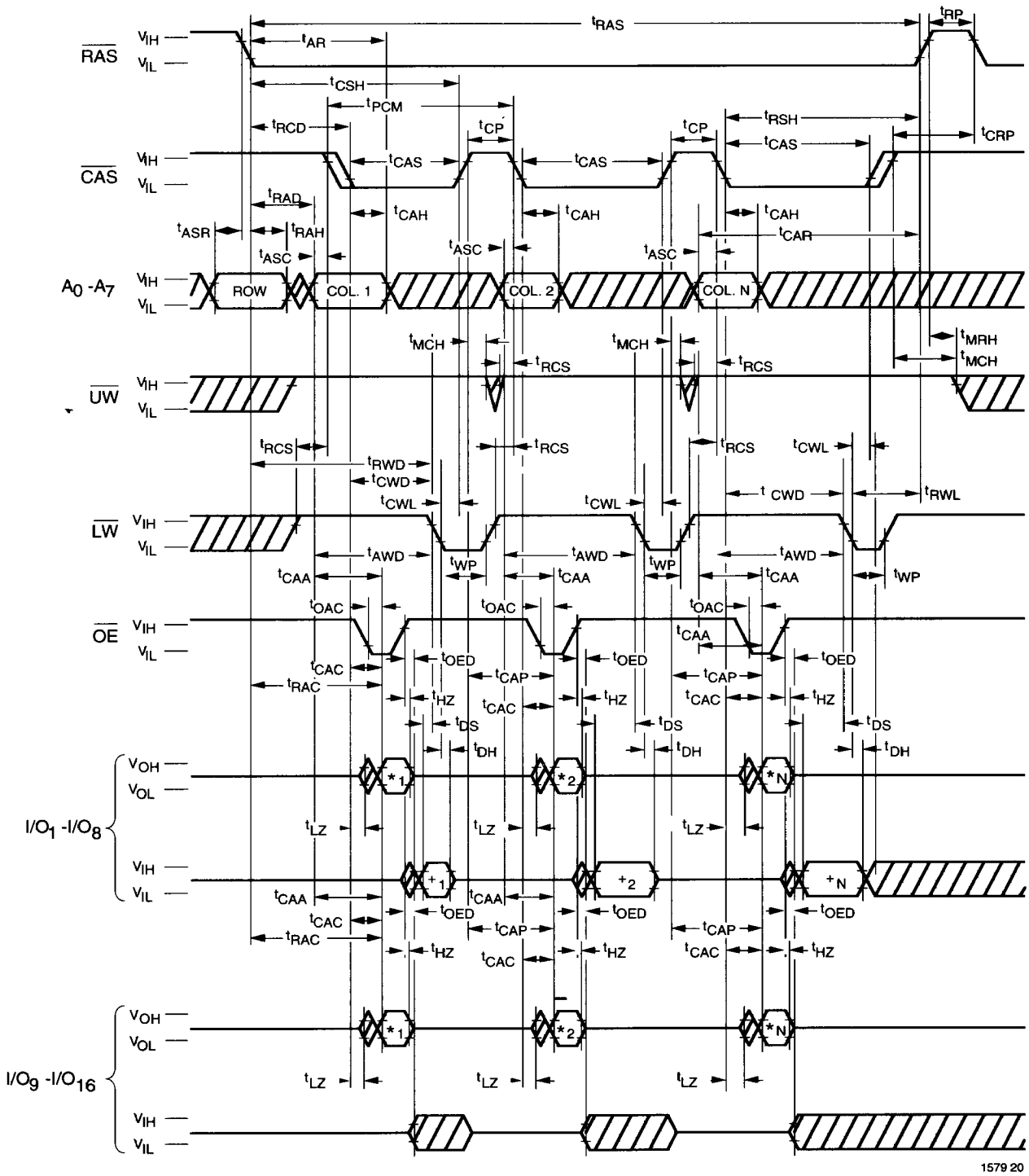
NOTE: * = D_{OUT}, + = D_{IN}

Fast Page Mode Read-Modify-Upper-Byte-Write Cycle



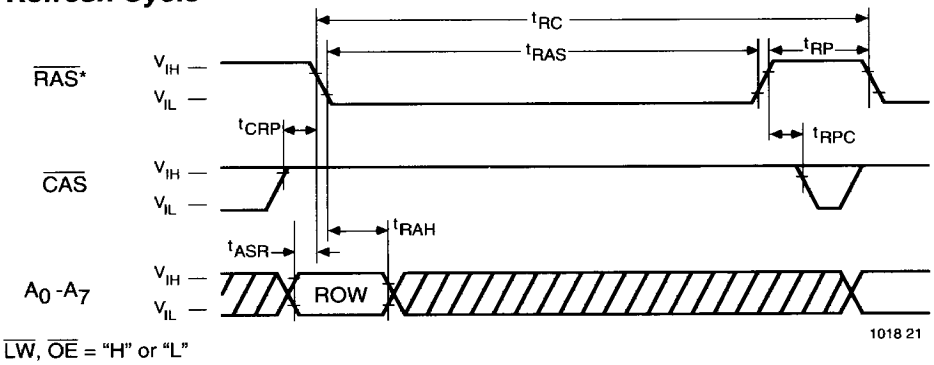
NOTE: * = D_{OUT}, + = D_{IN}

Fast Page Mode Read-Modify-Lower-Byte-Write Cycle



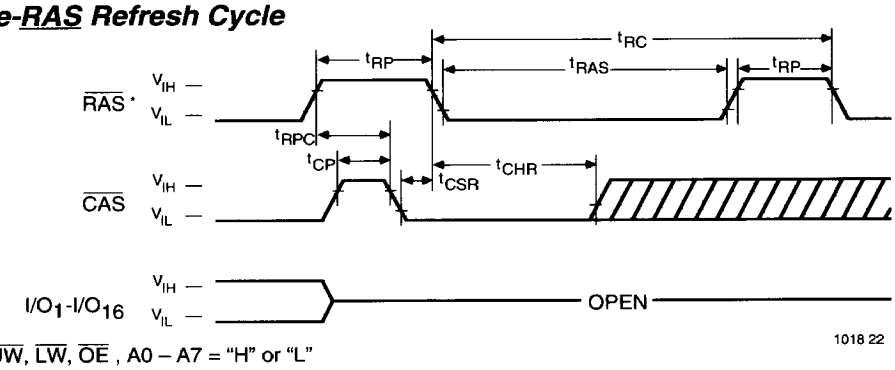
NOTE: * = D_{OUT}, + = D_{IN}

RAS-Only Refresh Cycle



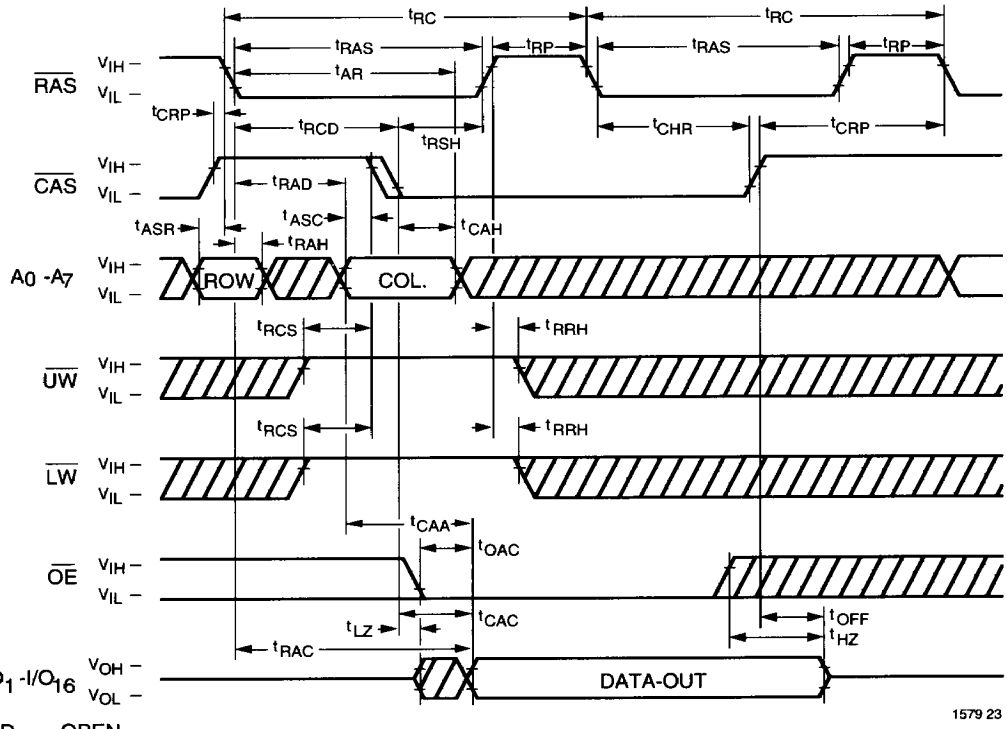
NOTE: $\overline{UW}$, $\overline{LW}$, $\overline{OE}$ = "H" or "L"

CAS-Before-RAS Refresh Cycle



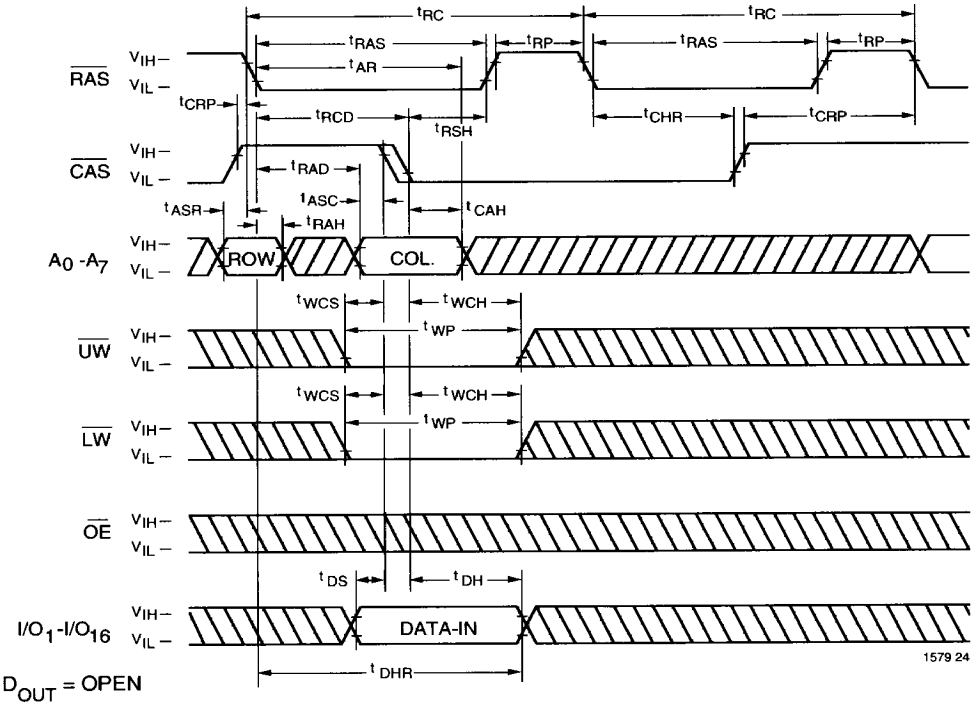
NOTE: D_{IN}, $\overline{UW}$, $\overline{LW}$, $\overline{OE}$, A0 – A7 = "H" or "L"

Hidden Refresh Cycle (Read)



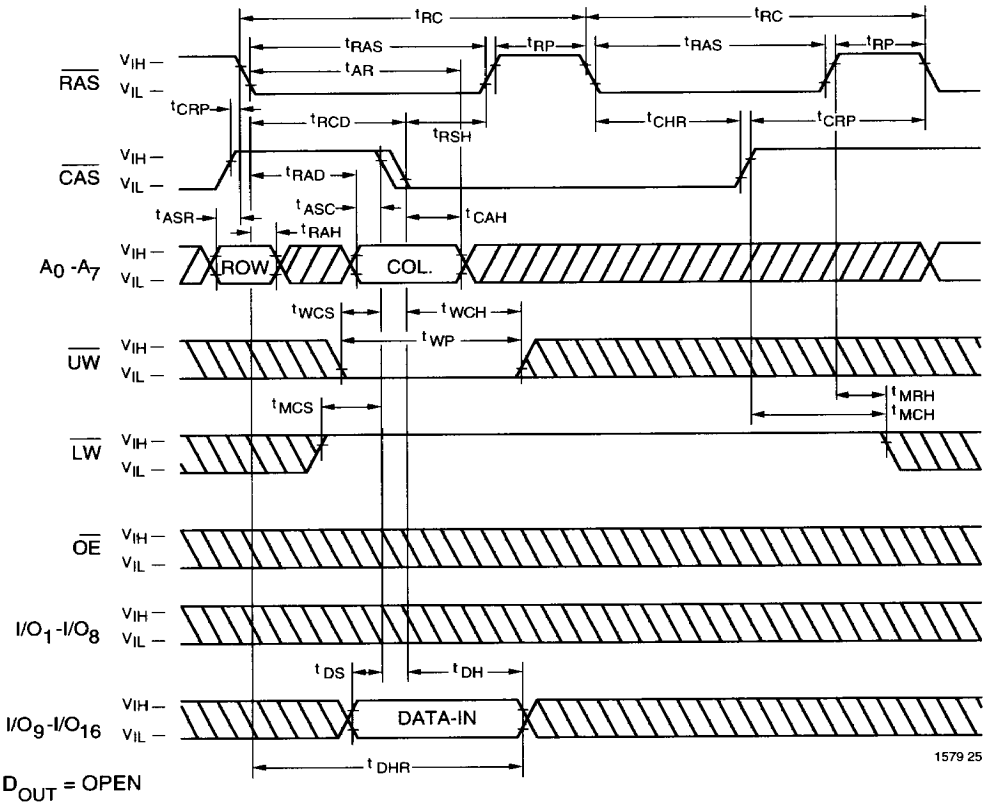
NOTE: D_{IN} = OPEN

Hidden Refresh Cycle (Write)



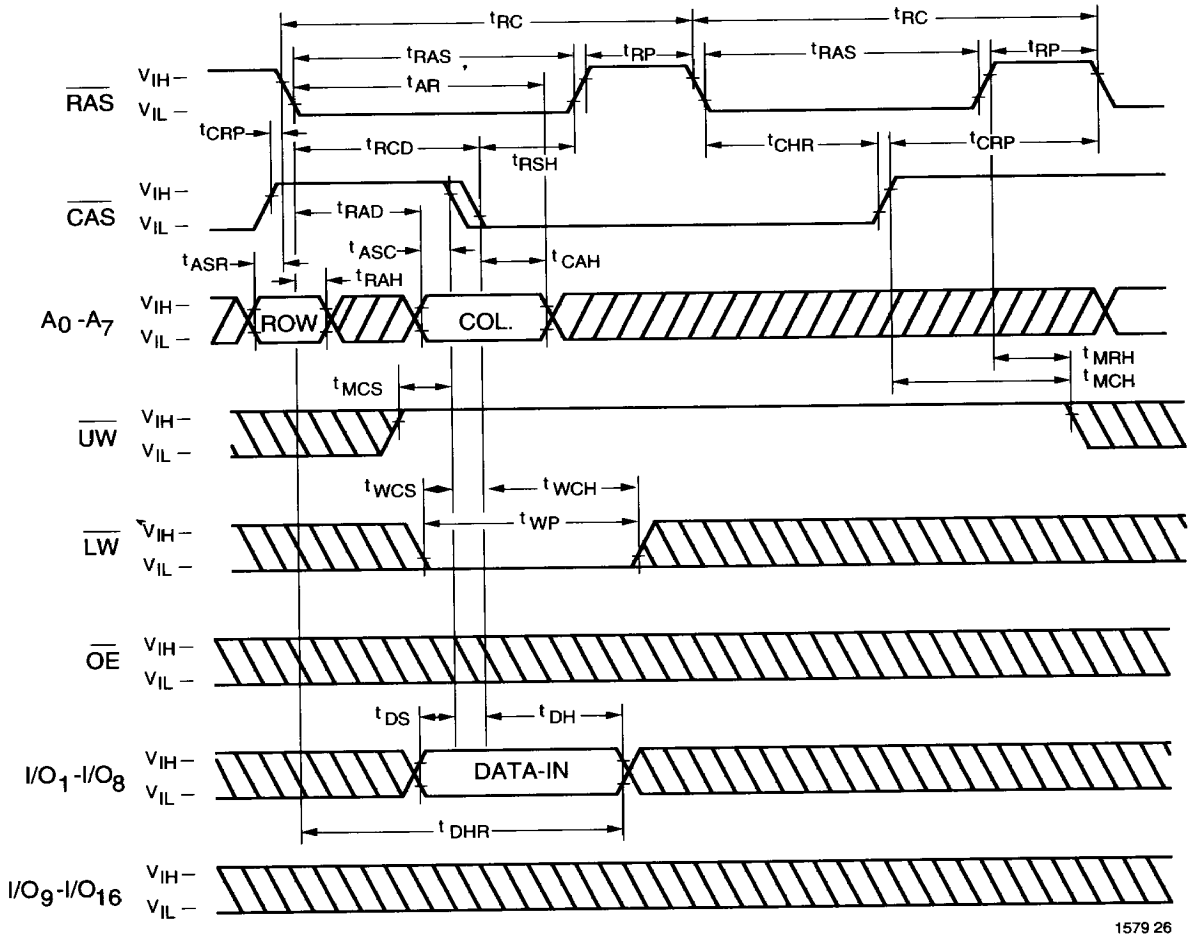
NOTE: D_{OUT} = OPEN

Hidden Refresh Cycle (Upper Byte Write)



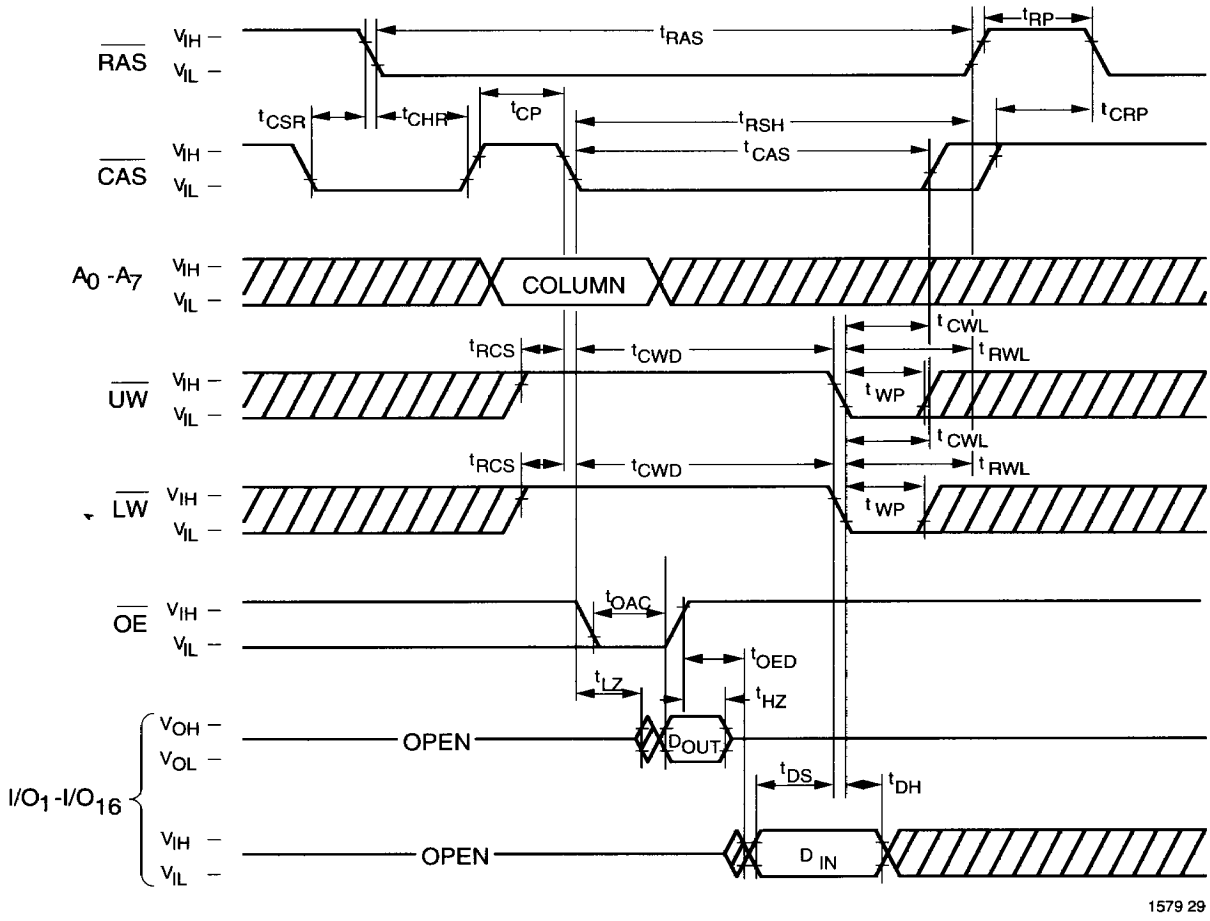
NOTE: D_{OUT} = OPEN

Hidden Refresh Cycle (Lower Byte Write)

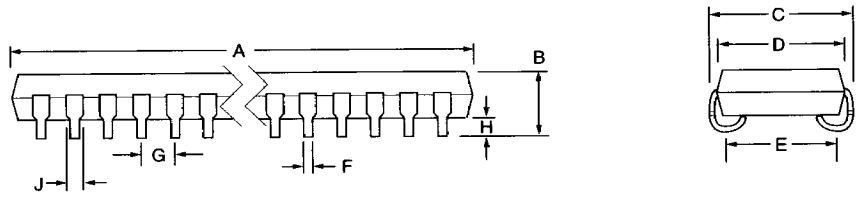


NOTE: D_{OUT} = OPEN

CAS-Before-RAS Refresh Counter Test Read-Modify-Write Cycle



Package Outline



(ADJUSTED VIEW)

40-pin SOJ

Dimension	Inches	Millimeters
A	1.025 Typ. 1.035 Max.	26.035 Typ. 26.289 Max.
B	0.145 Max.	3.683 Max.
C	0.434/0.446	11.024/11.328
D	0.395/0.405	10.033/10.287
E	0.357/0.379	9.608/9.627
F	0.016/0.022	0.406/0.559
G	0.050 Typ.	1.27 Typ.
H	0.026 Min.	0.66 Min.
J	0.020/0.032	0.508/0.813

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